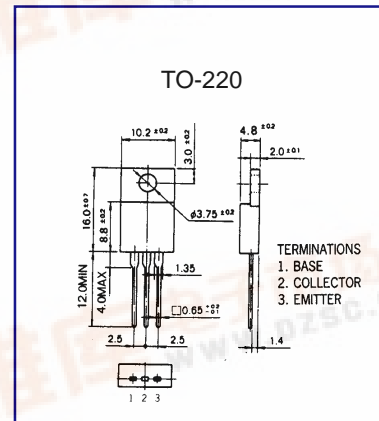




2SD288

NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER



ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	8 0	V
Collector-Emitter Voltage	VCEO	55	V
Emitter-Base voltage	VEBO	5	V
Collector Current (DC)	Ic	3	A
Collector Dissipation (Tc=25°C)	Pc	20	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-50~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	V _{CB} = 50V , I _E =0			50	μA
DC Current Gain	hFE1	V _{CE} = 5V , I _C =0.5A	40		240	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =1A , I _B =0.1A			1.0	
Current Gain Bandwidth Product						

